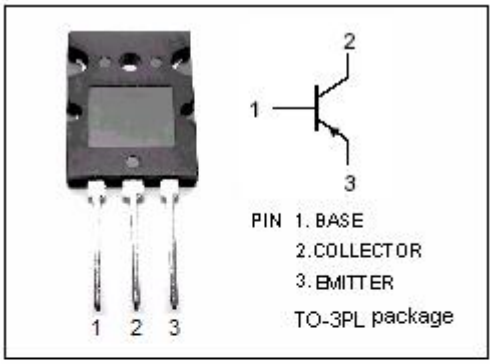
isc Silicon PNP Power Transistors — TIP36C*2



DESCRIPTION

- High Current Capability
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -100V(Min)
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

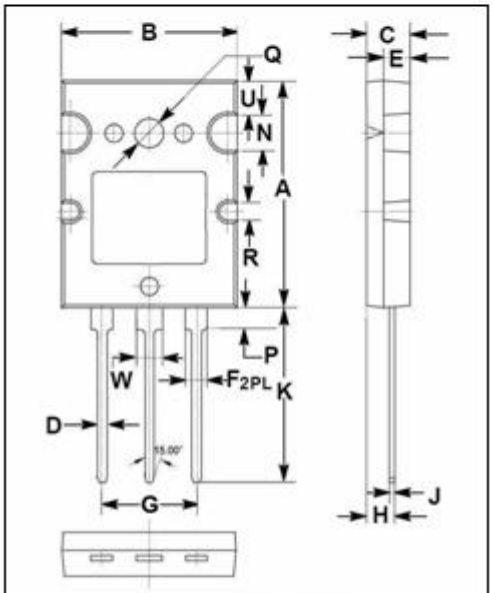
- Designed for use in general purpose power amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-40	A
I_{CM}	Collector Current-peak	-50	A
I_B	Base Current	-5	A
P_C	Collector Power Dissipation@T_C=25℃	200	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.0	℃/W



DIM	mm MIN	MAX
A	25.50	26.50
B	19.80	20.20
C	4.50	5.50
D	0.90	1.10
E	2.80	3.20
F	2.40	2.60
G	10.80	11.00
H	3.10	3.30
J	0.50	0.70
K	20.00	21.00
N	3.90	4.50
P	2.40	2.60
Q	3.10	3.50
R	1.90	2.60
U	3.90	4.10
W	2.90	3.25

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -30mA ;I_B= 0	-100		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -15A ;I_B= -1.5A		-1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -25A; I_B= -5A		-2.0	V
$V_{BE(on)-1}$	Base-Emitter On Voltage	I_C= -15A ; V_{CE}= -4V		-1.5	V
$V_{BE(on)-2}$	Base-Emitter On Voltage	I_C= -25A ; V_{CE}= -4V		-2.0	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -100V; I_B= 0		-0.1	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V; I_E= 0		-0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0		-0.1	mA
h_{FE-1}	DC Current Gain	I_C= -1.5A ; V_{CE}= -4V	60	200	
h_{FE-2}	DC Current Gain	I_C= -15A ; V_{CE}= -4V	30		
h_{FE-3}	DC Current Gain	I_C= -25A ; V_{CE}= -4V	15		
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A ; V_{CE}= -10V;f_{test}= 1.0MHz	10		MHz